

Photo Transistor Chip

Features

- Light Activated Photo Transistor Chip
- Planar NPN
- Aluminum Wire bondable
- Backside Metallization - Gold
- Die Attach methods: Eutectic or Epoxy

Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
BV_{CEO}	Collector-Emitter Voltage	$I_C = 100 \mu A$		500		Volts
BV_{EBO}	Emitter-Base Voltage	$I_E = 100 \mu A$		20		Volts
BV_{CBO}	Collector-Base Voltage	$I_C = 100 \mu A$		500		Volts
ID	Collector Current	$V_{CE} = 10 \text{ Volts}$		30		nAmps
h_{FE}	Beta	$V_{CE} = 5 \text{ Volts}, I_C = 1 \text{ mA}$		25		